

isc Silicon PNP Power Transistor

2SB856

DESCRIPTION

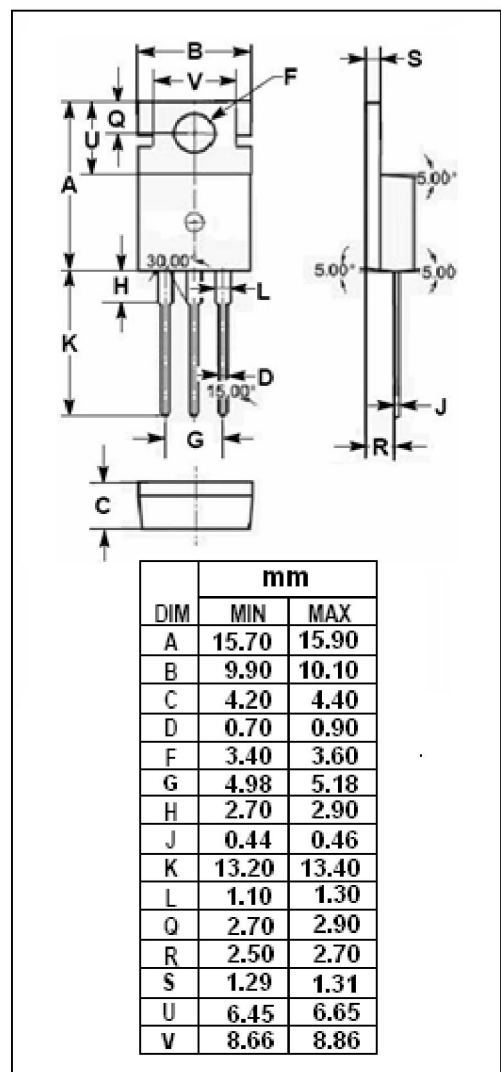
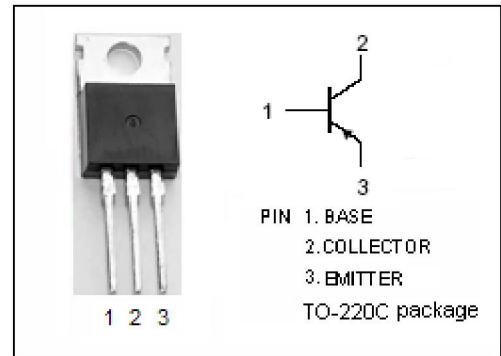
- Collector Current: $I_C = -3A$
- Low Collector Saturation Voltage
: $V_{CE(sat)} = -1.2V(Max) @ I_C = -2A$
- High Collector Power Dissipation

APPLICATIONS

- Designed for low frequency power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-3	A
P_C	Total Power Dissipation @ $T_C=25^{\circ}C$	25	W
T_J	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SB856****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -50\text{mA}$; $R_{BE} = \infty$	-50			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -5\text{mA}$; $I_E = 0$	-50			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -5\text{mA}$; $I_C = 0$	-4			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}$; $I_B = -0.2\text{A}$			-1.2	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}$; $V_{CE} = -4\text{V}$			-1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -20\text{V}$; $I_E = 0$			-100	μA
h_{FE-1}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -4\text{V}$	35		200	
h_{FE-2}	DC Current Gain	$I_C = -0.1\text{A}$; $V_{CE} = -4\text{V}$	35			
f_T	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}$; $V_{CE} = -4\text{V}$		35		MHz

◆ **h_{FE-1} Classifications**

A	B	C
35-70	60-120	100-200